## **Complementary Silicon Plastic Power Transistors**

These devices are designed for use in general purpose amplifier and switching applications.

#### **Features**

- High Current Gain Bandwidth Product
- These Devices are Pb-Free and are RoHS Compliant\*

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector–Emitter Voltage BD243B, BD244B BD243C, BD244C	V <sub>CEO</sub>	80 100	Vdc
Collector-Base Voltage BD243B, BD244B BD243C, BD244C	V <sub>CB</sub>	80 100	Vdc
Emitter-Base Voltage	V <sub>EB</sub>	5.0	Vdc
Collector Current - Continuous	Ic	6	Adc
Collector Current – Peak	I <sub>CM</sub>	10	Adc
Base Current	Ι <sub>Β</sub>	2.0	Adc
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	65 0.52	W W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

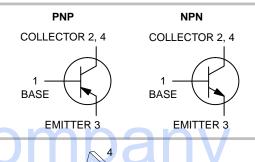
Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.92	°C/W

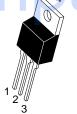


#### ON Semiconductor®

www.onsemi.com

# 6 AMPERE POWER TRANSISTORS COMPLEMENTARY SILICON 80-100 VOLTS 65 WATTS





TO-220 CASE 221A STYLE 1

#### **MARKING DIAGRAM**

BD24xyG AY WW BD24xy = Device Code x = 3 or 4y = B or C

A = Assembly Location Y = Year

WW = Work Week
G = Pb-Free Package

#### **ORDERING INFORMATION**

Device	Package	Shipping	
BD243BG	TO-220 (Pb-Free)	50 Units / Rail	
BD243CG	TO-220 (Pb-Free)	50 Units / Rail	
BD244BG	TO-220 (Pb-Free)	50 Units / Rail	
BD244CG	TO-220 (Pb-Free)	50 Units / Rail	

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

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Characteristic	Symbol	Min	Max	Unit
Collector–Emitter Sustaining Voltage (Note 1) ( $I_C = 30 \text{ mAdc}, I_B = 0$ ) BD243B, BD244B BD243C, BD244C	V <sub>CEO(sus)</sub>	80 100	- -	Vdc
Collector Cutoff Current $(V_{CE} = 60 \text{ Vdc}, I_B = 0)$ BD243B, BD243C, BD244B, BD244C	I <sub>CEO</sub>	_	0.7	mAdc
Collector Cutoff Current (V <sub>CE</sub> = 80 Vdc, V <sub>EB</sub> = 0) BD243B, BD244B (V <sub>CE</sub> = 100 Vdc, V <sub>EB</sub> = 0) BD243C, BD244C	lces		400 400	μAdc
Emitter Cutoff Current (V <sub>BE</sub> = 5.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	_	1.0	mAdc
ON CHARACTERISTICS (Note 1)			•	
DC Current Gain ( $I_C = 0.3$ Adc, $V_{CE} = 4.0$ Vdc) ( $I_C = 3.0$ Adc, $V_{CE} = 4.0$ Vdc)	h <sub>FE</sub>	30 15	- -	-
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 6.0 Adc, I <sub>B</sub> = 1.0 Adc)	V <sub>CE(sat)</sub>	-	1.5	Vdc
Base–Emitter On Voltage (I <sub>C</sub> = 6.0 Adc, V <sub>CE</sub> = 4.0 Vdc)	V <sub>BE(on)</sub>	-	2.0	Vdc
DYNAMIC CHARACTERISTICS	<u>.</u>			
Current–Gain – Bandwidth Product (Note 2) (I <sub>C</sub> = 500 mAdc, V <sub>CE</sub> = 10 Vdc, f <sub>test</sub> = 1.0 MHz)	f <sub>T</sub>	3.0	_	MHz
Small–Signal Current Gain (I <sub>C</sub> = 0.5 Adc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	h <sub>fe</sub>	20	_	-

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

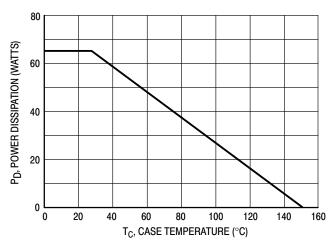
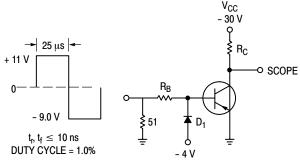


Figure 1. Power Derating

<sup>1.</sup> Pulse Test: Pulsewidth ≤ 300 μs, Duty Cycle ≤ 2.0%.

<sup>2.</sup>  $f_T = h_{fe} \bullet f_{test}$ 



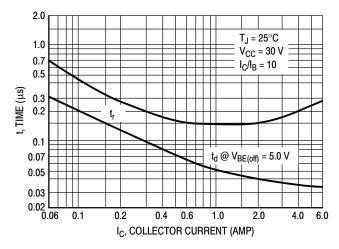
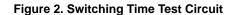


Figure 3. Turn-On Time



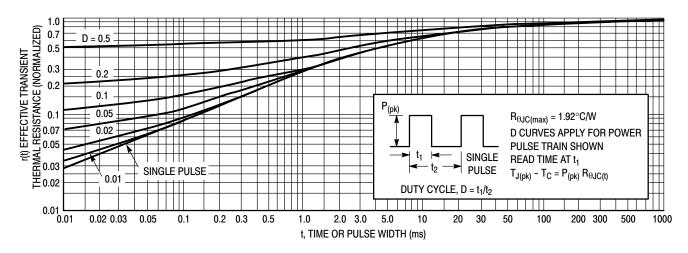


Figure 4. Thermal Response

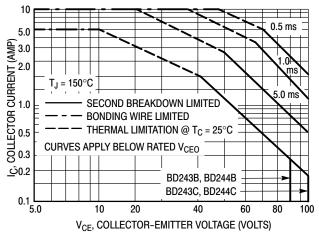


Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on  $T_{J(pk)} = 150^{\circ}\text{C}$ :  $T_{C}$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^{\circ}\text{C}$ ,  $T_{J(pk)}$  may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

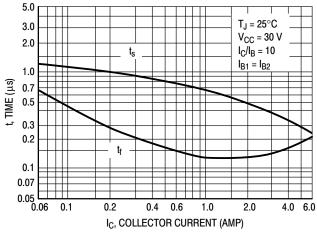


Figure 6. Turn-Off Time

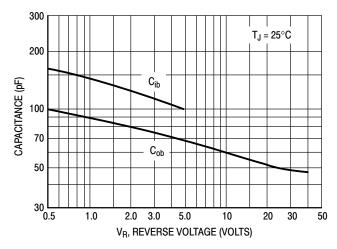


Figure 7. Capacitance

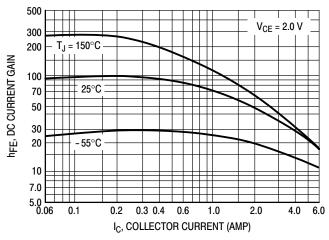


Figure 8. DC Current Gain

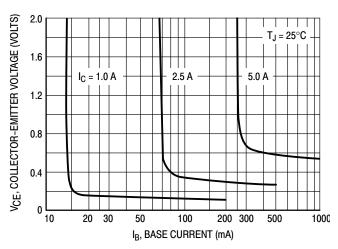


Figure 9. Collector Saturation Region

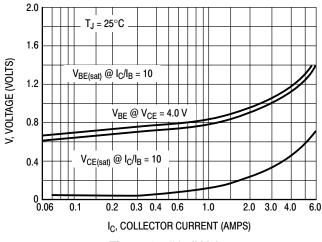


Figure 10. "On" Voltages

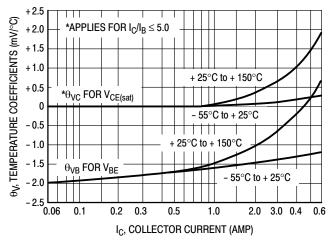
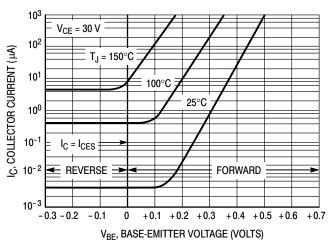


Figure 11. Temperature Coefficients





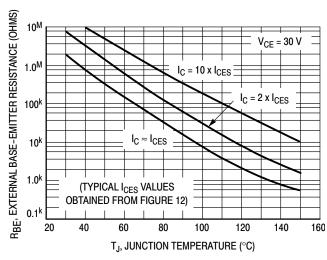
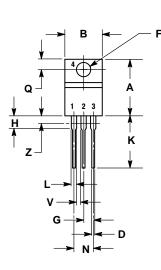
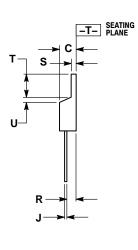


Figure 13. Effects of Base-Emitter Resistance

#### PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AH** 





- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
- DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE

MULIMETERS

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

STYLE 1:

BASE PIN 1.

- COLLECTOR
- **EMITTER** 3
- COLLECTOR

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